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(54) **SEMICONDUCTOR LIGHT-EMITTING ELEMENT**

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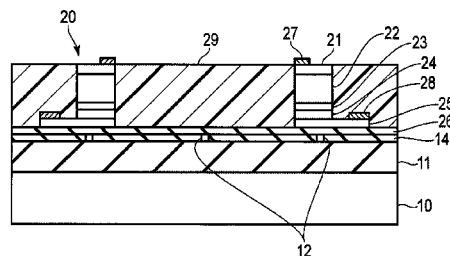
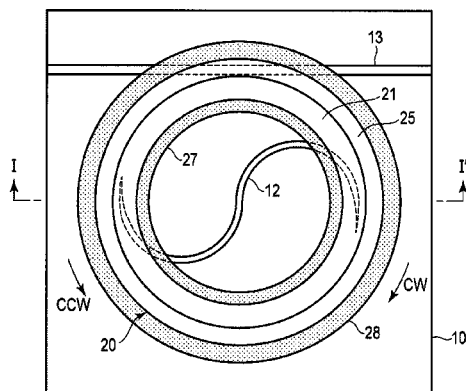
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(57) **ABSTRACT**

According to one embodiment, a semiconductor light-emitting element includes a ring-shaped light-emitting portion provided on a substrate, a mode-control light waveguide of Si provided on an upper or a lower surface side of the light-emitting portion, and including at least two portions located close to the light-emitting portion, and an output light waveguide of Si provided on the upper or the lower surface side, and including a portion located close to the
(Continued)



light-emitting portion. The mode-control light waveguide has a structure for coupling light traveling in one of a clockwise circulating mode and a counterclockwise circulating mode, and feeding back the light in the other of the clockwise circulating mode and the counterclockwise circulating mode.

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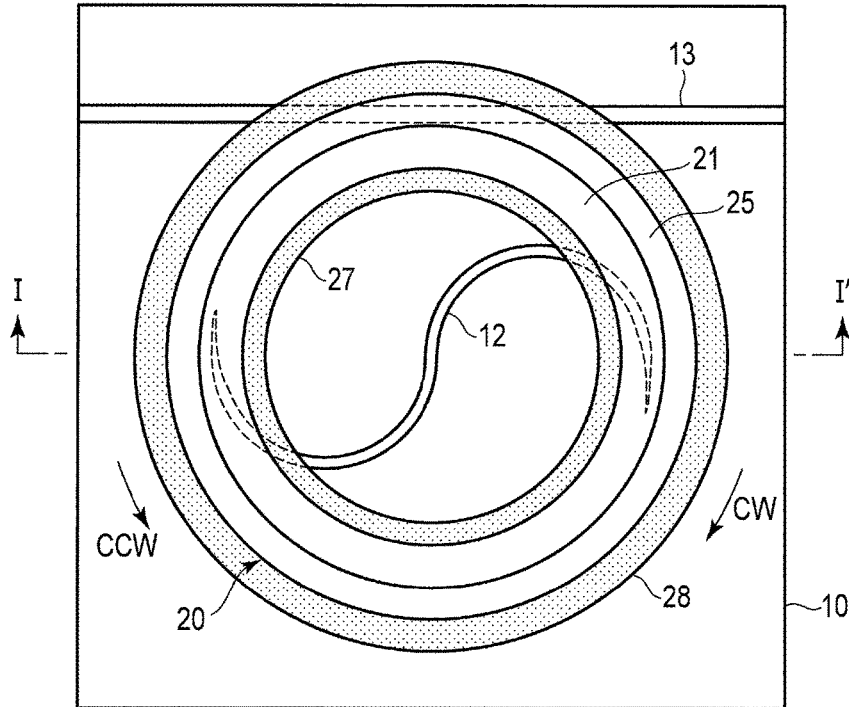


FIG. 1

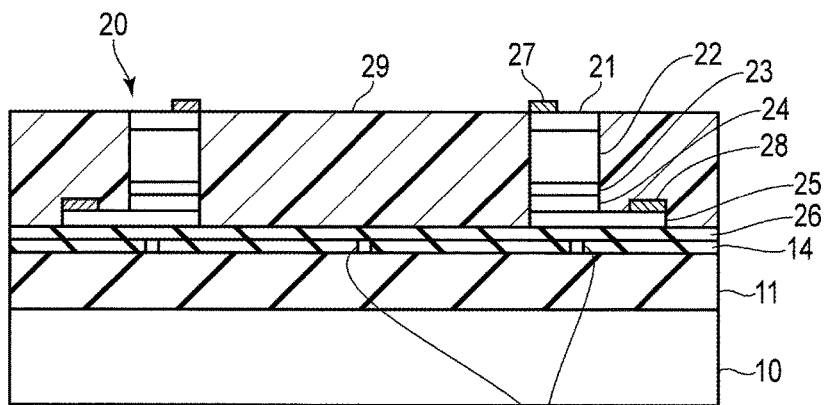


FIG. 2

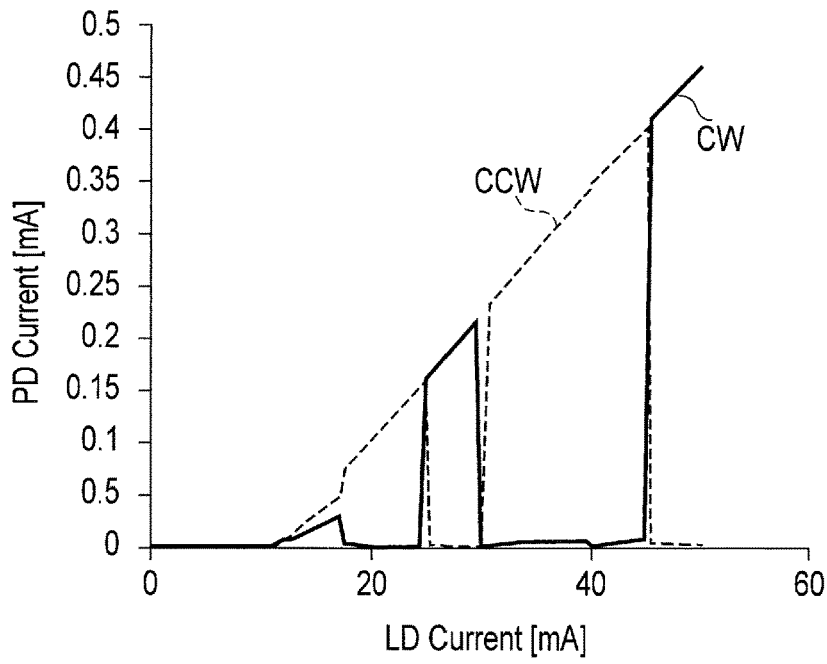


FIG. 3A

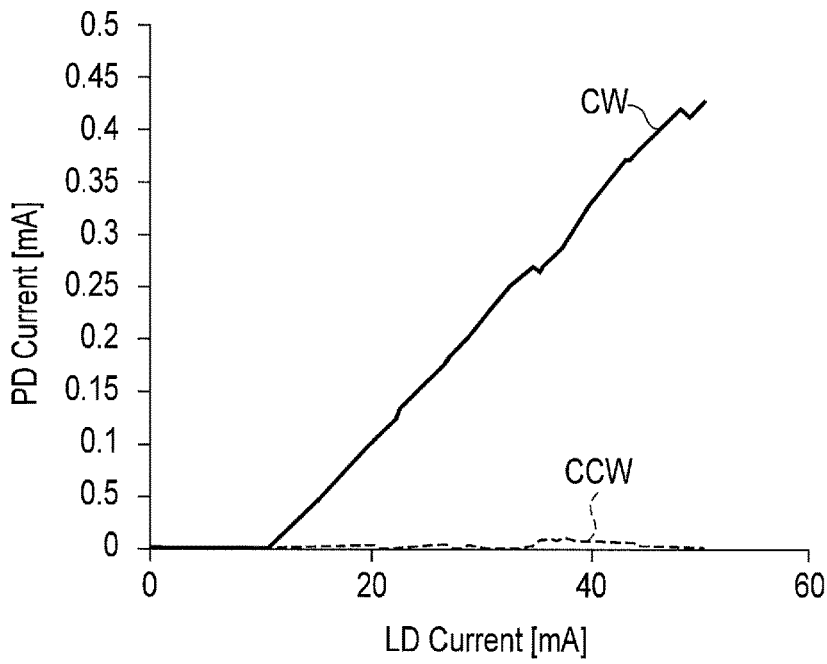


FIG. 3B

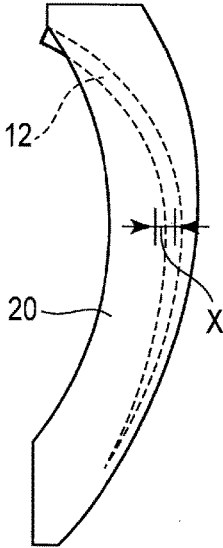


FIG. 4

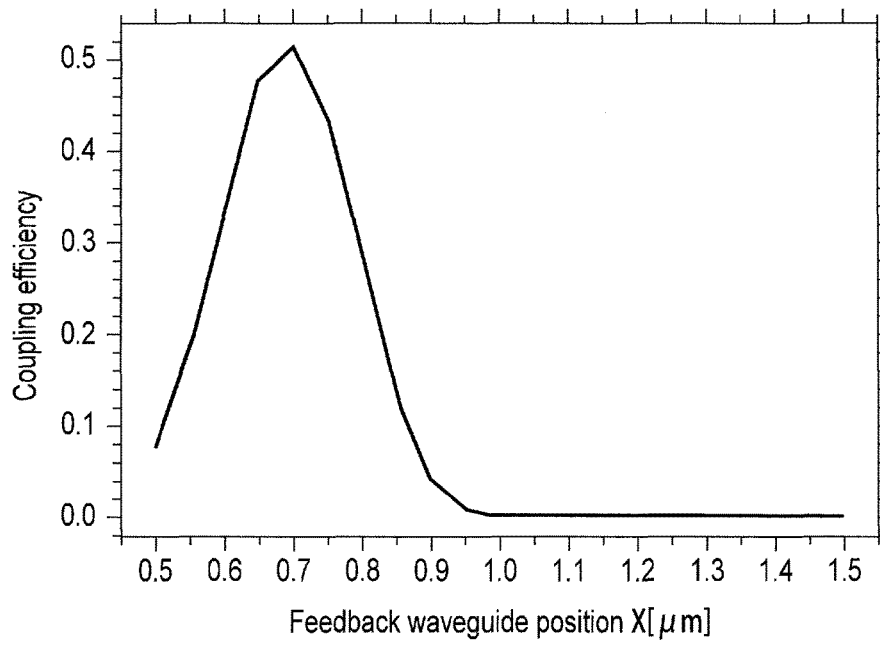


FIG. 5A

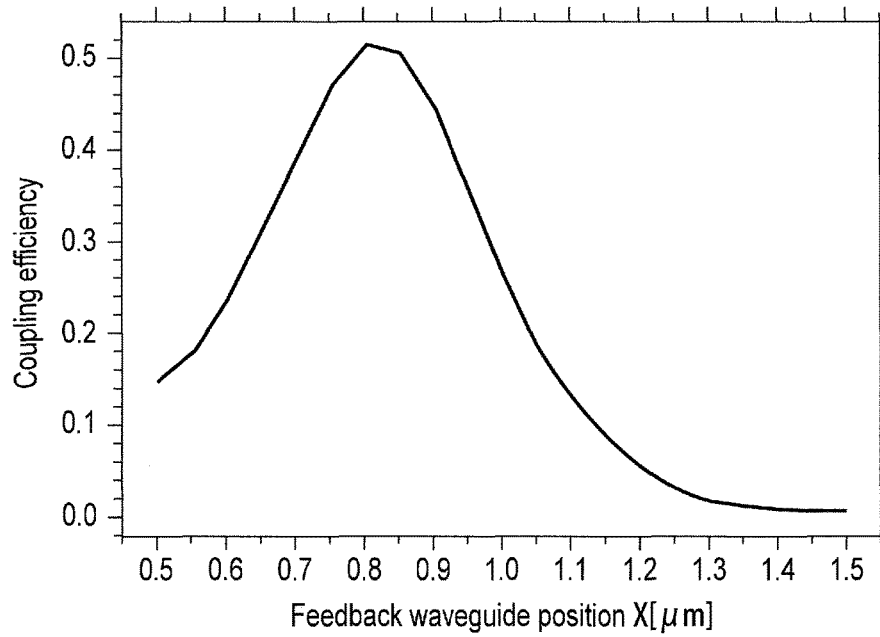


FIG. 5B

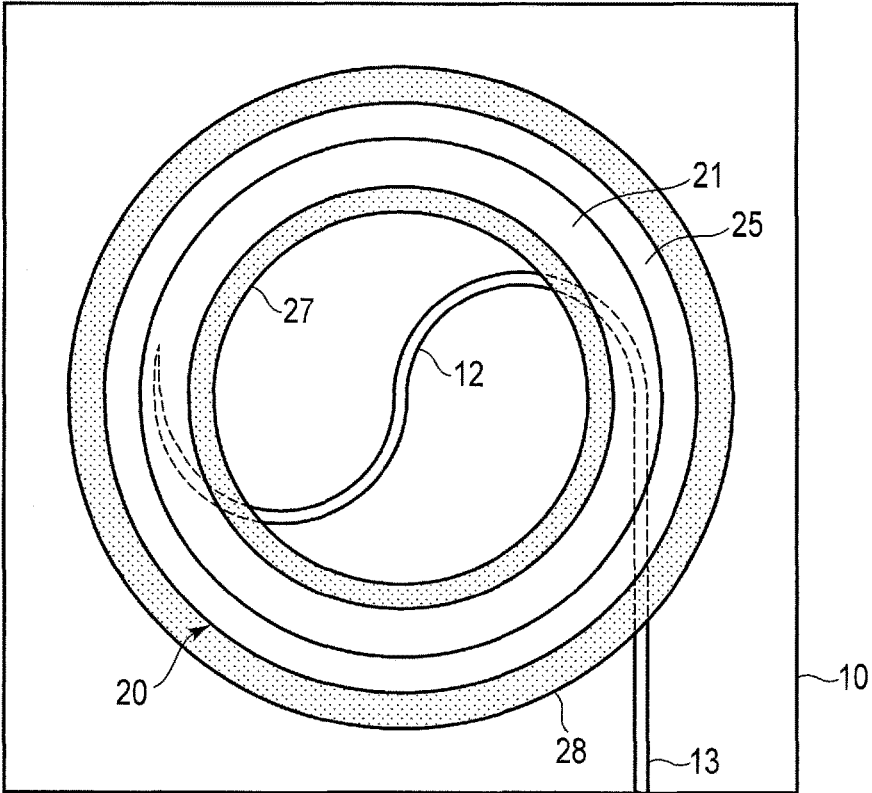


FIG. 6

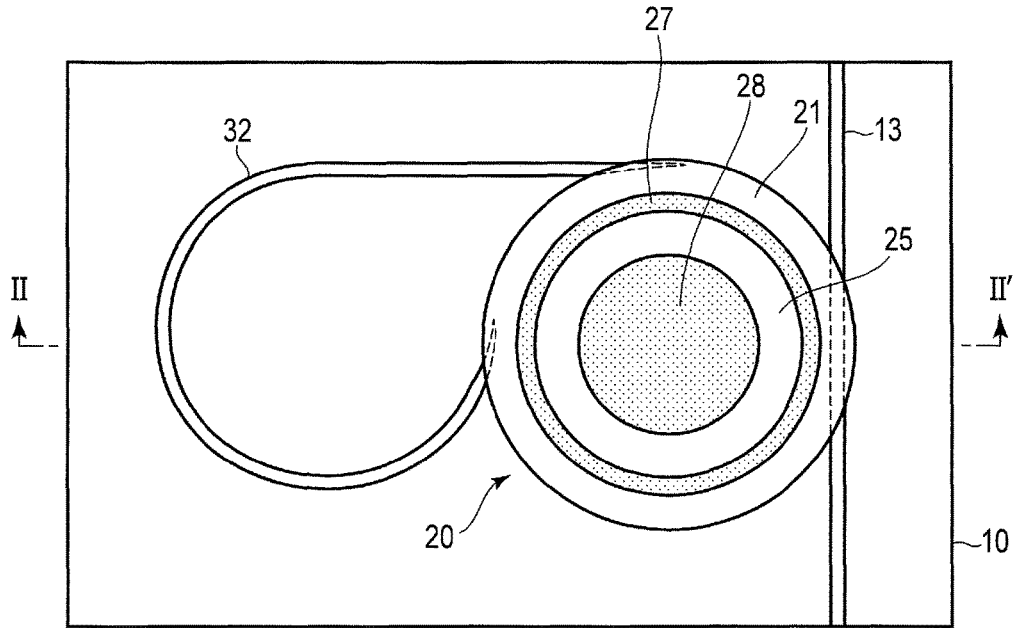


FIG. 7

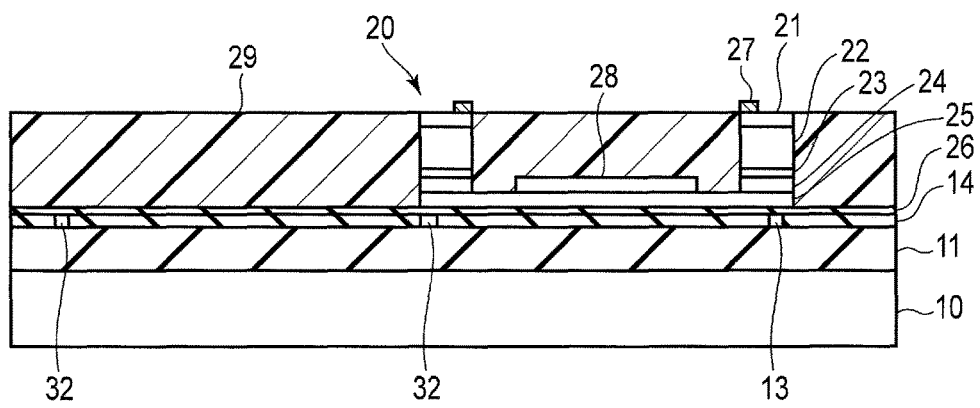


FIG. 8

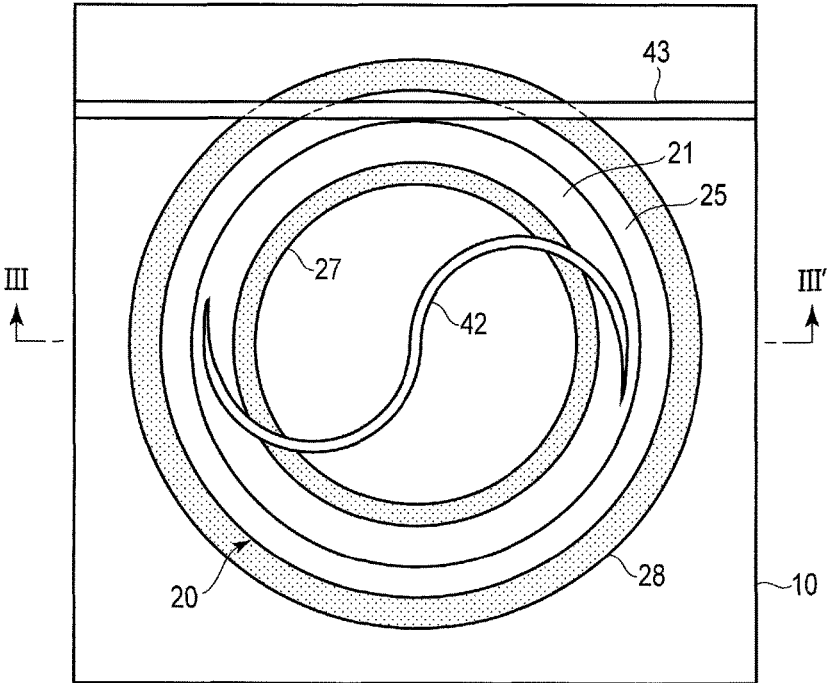


FIG. 9

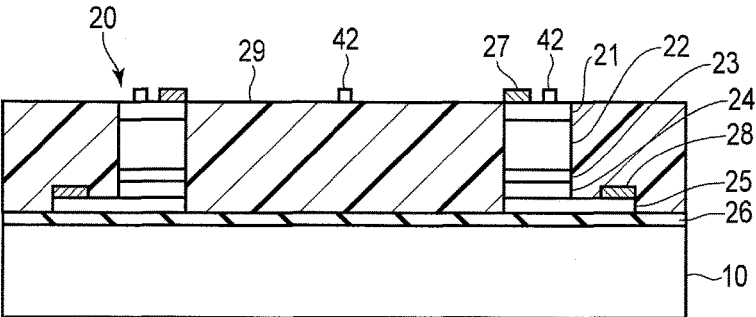


FIG. 10

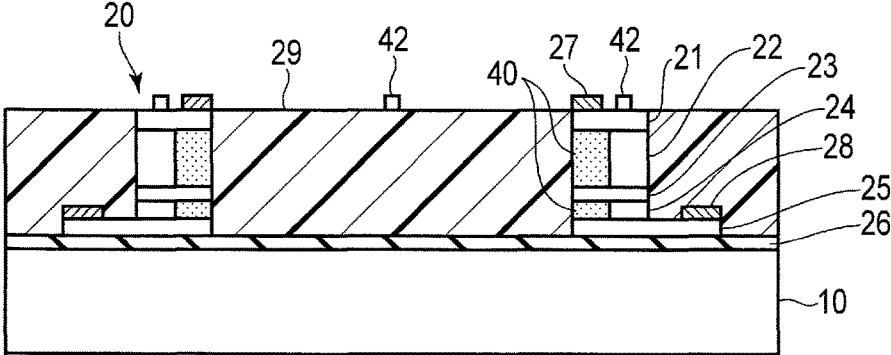


FIG. 11

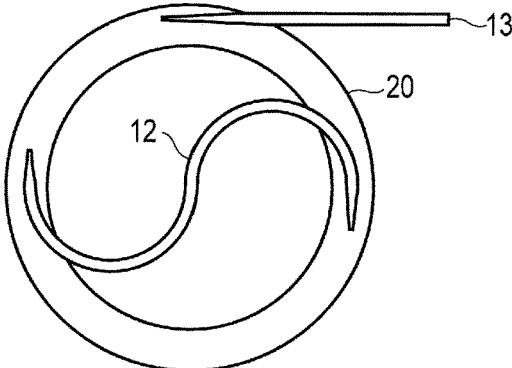


FIG. 12A

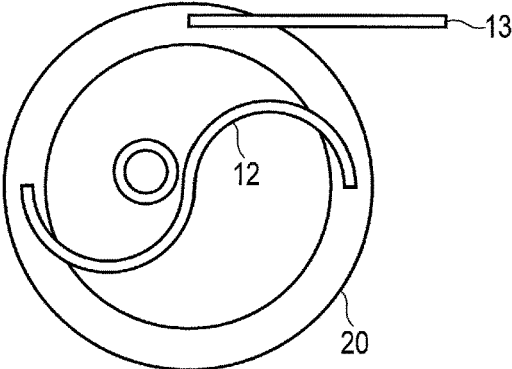


FIG. 12B

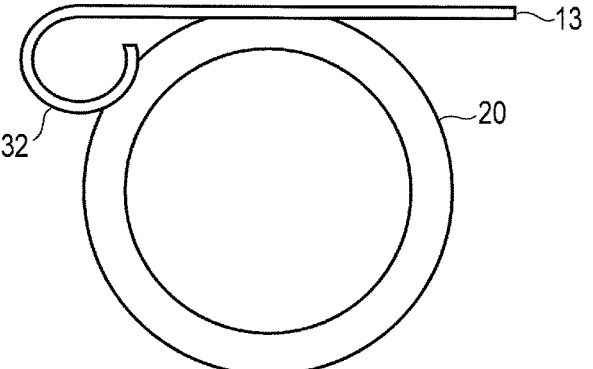


FIG. 12C

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SEMICONDUCTOR LIGHT-EMITTING ELEMENT

CROSS REFERENCE TO RELATED APPLICATIONS

This application is a Continuation Application of PCT Application No. PCT/JP2015/075568, filed Sep. 9, 2015 and based upon and claiming the benefit of priority from Japanese Patent Application No. 2014-190678, filed Sep. 19, 2014, the entire contents of all of which are incorporated herein by reference.

FIELD

Embodiments described herein relate generally to a semiconductor light-emitting element including a ring-shaped light-emitting portion.

BACKGROUND

In recent years, in order to achieve optical transmission at a low loss and a high density, various on-chip optical interconnects have been proposed in which data input and output are performed at a high speed and with a low power consumption. In order to achieve such an optical interconnect, attention is paid to a microring laser diode (LD) using a microring resonator, which is applied as a small light source. In this type of microring LD, the key to put it into practice is stabilization of circulating modes.

In order that stabilization of the circulating modes be improved, it has been proposed that in a microring LD, a light-emitting portion formed of a group III-V compound semiconductor and a feedback waveguide formed of a group III-V compound semiconductor are provided. However, in this structure, an absorption loss in the waveguide is great. Furthermore, the radius of curvature of the feedback waveguide cannot be greatly reduced. Thus, it is hard to make a microring resonator smaller.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a plan view illustrating a schematic configuration of a semiconductor light-emitting element according to a first embodiment.

FIG. 2 is a cross-sectional view illustrating the schematic configuration of the semiconductor light-emitting element according to the first embodiment.

FIG. 3A is a characteristic view showing a relationship between a drive current of a LD and a detection current of a PD (in the case where a Si feedback waveguide is not provided).

FIG. 3B is a characteristic view showing a relationship between the drive current of the LD and the detection current of the PD (in the case where a Si feedback waveguide is provided).

FIG. 4 is an enlarged plan view illustrating a distal end portion of the Si feedback waveguide.

FIG. 5A is a characteristic view showing a change of a coupling efficiency which is made in accordance with the set position of the Si feedback waveguide (in the case where the tapered distal end has the same radius of curvature as a ring-shaped resonator).

FIG. 5B is a characteristic view showing a change of the coupling efficiency which is made in accordance with the set position of the Si feedback waveguide (in the case where the

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tapered distal end has a radius of curvature different from that of the ring-shaped resonator).

FIG. 6 is a plan view illustrating a schematic configuration of a semiconductor light-emitting element according to a second embodiment.

FIG. 7 is a plan view illustrating a schematic configuration of a semiconductor light-emitting element according to a third embodiment.

FIG. 8 is a cross-sectional view illustrating the schematic configuration of the semiconductor light-emitting element according to the third embodiment.

FIG. 9 is a plan view illustrating a schematic configuration of a semiconductor light-emitting element according to a fourth embodiment.

FIG. 10 is a cross-sectional view illustrating the schematic configuration of the semiconductor light-emitting element according to the fourth embodiment.

FIG. 11 is a cross-sectional view illustrating a schematic configuration of a modification of the fourth embodiment.

FIG. 12A is a plan view illustrating a modification of the Si feedback waveguide.

FIG. 12B is a plan view illustrating another modification of the Si feedback waveguide.

FIG. 12C is a plan view illustrating still another modification of the Si feedback waveguide.

DETAILED DESCRIPTION

In general, according to one embodiment, a semiconductor light-emitting element comprises: a ring-shaped light-emitting portion provided on part of a substrate; a mode-control light waveguide formed of Si and provided on an upper surface side or a lower surface side of the light-emitting portion, and including at least two portions located close to the light-emitting portion; and an output light waveguide formed of Si and provided on the upper surface side or the lower surface side of the light-emitting portion, and including a portion located close to the light-emitting portion, wherein the mode-control light waveguide has a structure for coupling light traveling in one of a clockwise circulating mode and a counterclockwise circulating mode of the light-emitting portion, and feeding back the light in the other of the clockwise circulating mode and the counterclockwise circulating mode.

Embodiments will be hereinafter described with reference to the accompanying drawings.

First Embodiment

FIGS. 1 and 2 are views for explaining a schematic configuration of a semiconductor light-emitting device according to a first embodiment. FIG. 1 is a plan view illustrating a relationship between a light-emitting portion and a waveguide, and FIG. 2 is a cross-sectional view which is taken along line I-I' as seen in the direction of arrows in FIG. 1. It should be noted that FIG. 1 illustrates only a characteristic portion in order that the following explanation be understandable.

An insulating film 11 formed of a SiO₂ or the like is provided on a Si substrate 10. On the insulating film 11, an S-shaped Si feedback waveguide (mode-control optical waveguide) 12 and a Si output waveguide (output optical waveguide) 13 are formed. To be more specific, a Si layer formed of SOI is processed to be S-shaped, to thereby form the Si feedback waveguide 12. Also, a Si layer formed of SOI is processed to be linear, to thereby form a Si output waveguide 13 for use in outputting light from a ring laser

diode (LD [light emitting unit]) to be described later, to the outside. Each of the waveguides **12** and **13** has a width of, for example, 600 nm and a height of, for example, 400 nm. In areas laterally adjacent to the waveguides **12** and **13**, oxide films **14** formed of SiO₂ are embedded, as a result of which their surfaces are flat.

It should be noted that a Si substrate **10** is provided to extend to a region not illustrated. In a region of the Si substrate **10** which is other than a region in which the semiconductor light-emitting element is provided, the semiconductor photodetector and other active elements are formed. Also, for example, the Si output waveguide **13** is optically coupled to a semiconductor light receiving element.

To a region of the substrate in which the waveguides **12** and **13** are formed, a ring-shaped semiconductor multilayered structure **20** is joined, which forms a light-emitting unit of a microring LD. In the semiconductor multilayered structure (light-emitting unit) **20**, a double-heterostructure portion in which an InGaAs active layer **23** is held between a p-type GaAlAs clad layer **22** and an n-type GaAlAs clad layer **24** is provided, and the double-heterostructure portion is held between a p-type GaAs contact layer **21** and an n-type GaAs contact layer **25**. Also, the semiconductor multilayered structure **20** is joined to the region of the substrate in which the waveguides **12** and **13** are formed, with the contact layer **25** located on a lower side.

It should be noted that the active layer **23** need not always be a single layer; i.e., it may have a structure in which an InGaAs/GaAs multiple quantum well layer is held between GaAlAs clad layers. Furthermore, in the semiconductor multilayered structure **20**, the type of the p-type layers may be changed to n-type, and the type of the n-type layers may be changed to p-type.

The n-type GaAs contact layer **25** located on the lower side is provided to outwardly project from the ring of the semiconductor multilayered structure **20**. On a projected portion of the contact layer **25**, an n-side electrode **28** is provided, and formed in the shape of a ring. Also, on the p-type GaAs contact layer **21**, a p-side electrode **27** is provided, and formed in the shape of a ring.

Furthermore, space located inward and outward of the semiconductor multilayered structure **20** is filled with insulating films **29** formed of polyimide. Furthermore, a junction portion of the semiconductor multilayered structure **20**, which is an underlying substrate, is an oxide film **26** formed of SiO₂ or the like. The oxide film **26** is joined to the underlying structure.

It should be noted that in the case where the semiconductor multilayered structure **20** is joined to the underlying structure, a p-type GaAs contact layer **21** having a thickness of 200 nm, a p-type GaAlAs clad layer **22** having a thickness of 1.6 μm, an InGaAs active layer **23** having a thickness of 5 nm, an n-type GaAlAs clad layer **24** having a thickness of 250 nm, and an n-type GaAs contact layer **25** having a thickness of 200 nm are formed on a GaAs substrate (not shown), and then the n-type GaAs contact layer is joined to the underlying substrate. In this case, it is preferable that a nitride film formed of SiN or the like or an oxide film **26** formed of SiO₂ or the like be formed on the n-type GaAs contact layer **25**. Furthermore, in the underlying structure, an oxide film **14** formed of SiO₂ or the like be embedded in areas laterally adjacent to the waveguides **12** and **13**, and its surface be flattened. After the above joining process, the GaAs substrate is removed, and the semiconductor multilayered structure **20** is processed to be shaped in the form of a ring. This processing is executed such that an outer

periphery of the n-type GaAs contact layer **25** more outwardly project than those of the other layers, i.e., the above layers **21** to **24**.

The Si feedback waveguide **12** is S-shaped, and located inward of the semiconductor multilayered structure **20**, such that the S-shaped waveguide **12** and the semiconductor multilayered structure **20** overlap with each other at both ends of the waveguide **12**. Also, both end portions of the Si feedback waveguide **12** are tapered. Furthermore, the radius of curvature of the both end portions of the Si feedback waveguide **12** is greater than that of the semiconductor multilayered structure **20**, which is formed in the shape of a ring. The Si output waveguide **13** is provided such that the Si output waveguide **13** and the semiconductor multilayered structure **20** overlap with each other.

The microring LD has a clockwise (CW) circulating mode and a counterclockwise (CCW) circulating mode. However, in the first embodiment, these circulating modes are forcibly limited to one by the S-shaped Si feedback waveguide **12**. To be more specific, in the microring LD, CCW circulating light enters the Si feedback waveguide **12**, and is fed back to a light-emitting portion **20** as CW circulating light. By contrast, most of CW circulating light does not enter the Si feedback waveguide **12**. Thus, the CW circulating mode is given higher priority than the CCW circulating mode.

FIGS. **3A** and **3B** illustrate a difference between CW and CCW circulating-mode characteristics obtained in the cases where the Si feedback waveguide **12** is present and where it is absent. To be more specific, in the case where the Si feedback waveguide **12** is absent, as illustrated in FIG. **3A**, the CW circulating mode and the CCW circulating mode are both established, and oscillation becomes unstable. By contrast, in the first embodiment, the Si feedback waveguide **12** is provided, as illustrated in FIG. **3B**, the CW circulating mode becomes dominant, and the CCW circulating mode almost disappears. Thus, oscillation in the microring LD is stabilized.

Furthermore, since the feedback waveguide **12** is formed of Si, the absorption loss in the waveguide **12** can be reduced, as compared with the case where the feedback waveguide **12** is formed of a group III-V compound semiconductor. The above can be achieved by joining the semiconductor multilayered structure **20** formed on the GaAs substrate to an SOI substrate using a technique for bonding substrates to each other.

In addition, in the first embodiment, since a distal end portion of the Si feedback waveguide **12** is tapered, it is possible to reduce reflection at the distal end of the waveguide. Also, since the radius of curvature of the distal end is set great, the following advantage can also be obtained.

FIG. **4** is an enlarged view illustrating the distal end portion of the Si feedback waveguide **12** along with part of the semiconductor multilayered structure **20**. It is assumed that in the case where the radius of curvature of the distal end portion of the Si feedback waveguide **12** is equal to that of the semiconductor multilayered structure **20**, a circumferential center position of the ring-shaped semiconductor multilayered structure **20** which is intermediate between an inner circumferential portion and an outer circumferential portion of the semiconductor multilayered structure **20** is coincident with a center position of the distal end portion, and they are parallel to each other. Also, it is assumed that displacement of the center position of the distal end portion from the circumferential center position of the semiconductor multilayered structure **20**, which occurs in the case where

the radius of curvature of the distal end portion is different from that of the semiconductor multilayered structure **20**, is x .

FIGS. **5A** and **5B** are views showing a feedback waveguide position (X) dependence of an optical coupling efficiency from the semiconductor multilayered structure to the Si feedback waveguide, which is calculated by a beam-propagation method.

In the following, it is assumed that a Si feedback waveguide position (X) is a distance between the center of the Si feedback waveguide **12** and the circumferential center of a ring resonator, in a location at which the Si feedback waveguide **12** and the ring resonator (the semiconductor multilayered structure **20**) are parallel to each other.

When $X=0$, the circumferential center of the ring resonator is coincident with the center of the Si feedback waveguide **12**, and when $X>0$, the center of the Si feedback waveguide **12** is shifted to the outside of the ring resonator.

It is assumed that the ring resonator has a ring diameter of $50\ \mu\text{m}$ and a mesa width of $2\ \mu\text{m}$, and the Si feedback waveguide **12** is a rib type waveguide having a width of $600\ \text{nm}$, a slab thickness of $200\ \text{nm}$ and a mesa height of $200\ \text{nm}$.

FIG. **5A** shows an optical coupling efficiency in the case where the tapered distal end has the same radius of curvature ($R=25\ \mu\text{m}$) as the ring resonator, i.e., in the case where the tapered distal end of the Si feedback waveguide **12** is provided parallel to the circumferential center of the ring resonator. FIG. **5B** shows an optical coupling efficiency in the case where the radius of curvature of the tapered distal end is set to a value (R to $27.5\ \mu\text{m}$) which is greater than that of the ring resonator by approximately ten percent, and the tapered distal end of the Si feedback waveguide **12** obliquely crosses the circumferential center of the ring resonator.

If X is displaced by $100\ \text{nm}$ from a feedback waveguide position (X) at which the coupling efficiency is the maximum, in the case shown in FIG. **5A**, the coupling efficiency lowers by approximately 50%, and in the case shown in FIG. **5B**, the coupling efficiency lowers by approximately 13%; that is, lowering of the coupling efficiency is reduced. In such a manner, the shape of part of the Si feedback waveguide **12** in which optical coupling is carried out is adjusted, thereby reducing displacement from design, which occurs in an element processing process. For example, even if displacement of 50 to $100\ \text{nm}$ occurs in alignment using a stepper, it is possible to reduce a change of an element characteristic. That is, it is possible to ensure a sufficient process margin.

In such a manner, according to the first embodiment, a microring LD is formed using a semiconductor multilayered structure **20** comprising stacked layers formed in the shape of a ring, and in the microring LD, an S-shaped Si feedback waveguide **12** is formed such that optical coupling can be achieved, to thereby provide a semiconductor light-emitting element in which circulating modes are stable. In this case, as the feedback waveguide **12**, a Si waveguide is used which has a higher refractive index than that of a III-V compound semiconductor, and is thinner than the III-V compound semiconductor. Thereby, light loss in the feedback waveguide **12** can be reduced, and the radius of S-shaped part can be reduced. This results in reduction of the diameter of the ring of the light-emitting portion. It is therefore advantageous in reduction of the size of a device structure.

Furthermore, since the distal end portion of the Si feedback waveguide **12** is tapered, it is possible to reduce reflection at the distal end of the waveguide, and also reduce returning light. Also, since the radius of curvature of the distal end is set great, the process margin can be improved.

Furthermore, since the Si waveguide **12** is formed in a substrate other than a substrate where the light-emitting portion is formed in a region of the substrate which is other than a region in which where the light-emitting portion is formed), the waveguide **12** can be designed in width and location with a high degree of flexibility. Therefore, a proper feedback intensity can be easily achieved by appropriately designing the width and location of the waveguide **12**.

Second Embodiment

FIG. **6** is a plan view for explaining a schematic configuration of a semiconductor light-emitting element according to a second embodiment, and also shows a relationship between a light-emitting portion and a waveguide. It should be noted that elements identical to the elements explained above will be respectively denoted by the same reference numbers as the explained elements, and their detailed explanations will be omitted.

In the second embodiment, a Si feedback waveguide **12** and a Si output waveguide **13** are formed as a single body. In this regard, the second embodiment is different from the first embodiment. To be more specific, at one of ends of the Si feedback waveguide **12**, a ring-shaped light-emitting portion (semiconductor multilayered structure) **20** and the Si feedback waveguide **12** overlap with each other as in the first embodiment, and its distal end is tapered. Also, at the other end of the Si feedback waveguide **12**, the light-emitting portion and the Si feedback waveguide **12** overlap with each other; however, the other end of the Si feedback waveguide is continuous with the Si output waveguide **13**, which is linearly formed. It should be noted that elements other than the waveguide have the same structures as those as illustrated in FIG. **2**.

By virtue of such a structure, in the second embodiment, the effect similar to the first embodiment is obtained. Further, in the waveguides **12** and **13** and the light-emitting portion **20**, the number of portions where optical coupling is carried out can be reduced. This results in reduction of a coupling loss in optical-coupling portions.

Third Embodiment

FIGS. **7** and **8** are views for explaining a schematic configuration of a semiconductor light-emitting element according to a third embodiment. FIG. **7** is a plan view showing a relationship between a light-emitting portion and a waveguide, and FIG. **8** is a cross-sectional view which is taken along line II-II' as seen in the direction of arrows in FIG. **7**. It should be noted that elements identical to those in FIGS. **1** and **2** will be respectively denoted by the same reference numbers as those in FIGS. **1** and **2**, and their detailed explanations will be omitted.

In the third embodiment, a Si feedback waveguide **12** is provided not only inward of a ring-shaped light-emitting portion **20** but outward of the light-emitting portion **20**. In this regard, the third embodiment is different from the first embodiment. To be more specific, a C-shaped Si feedback waveguide **32** is provided outward of the ring-shaped light-emitting portion **20**, such that the light-emitting portion **20** and the Si feedback waveguide **32** overlap with each other at both ends of the waveguide **32**. Also, the both ends of the Si feedback waveguide **32** are provided to extend along the CW direction of a ring LD, and their distal ends are tapered.

Furthermore, unlike layers **21** to **24** in the light-emitting portion **20**, an n-type GaAs contact layer **25** is continuously

formed such that its inner side is not removed. In addition, on an inner portion of the contact layer **25**, an n-side electrode **28** is provided.

Even in such a structure, because of provision of the C-shaped Si feedback waveguide **32**, a CW circulating mode can be selected, and a stable operation can be carried out. Therefore, the third embodiment can also obtain the same advantage as the first embodiment. Furthermore, since the Si feedback waveguide **32** is provided outward of the ring-shaped light-emitting portion **20**, its radius can be set great. Therefore, it is possible to further reduce light output from the Si feedback waveguide **32**.

Furthermore, the radius of the light-emitting portion **20** can be set small regardless of the radius of the Si feedback waveguide **32**. Thereby, it is possible to emit light with smaller current. In addition, a resonant wavelength interval of the microring LD is great, whereby between different resonant wavelengths, hopping of an oscillation wavelength does not easily occur. Therefore, the operation is stabilized.

Fourth Embodiment

FIGS. **9** and **10** are views for explaining a schematic configuration of a semiconductor light-emitting element according to a fourth embodiment. FIG. **9** is a plan view showing a relationship between a light emitting portion and a waveguide, and FIG. **10** is a cross-sectional view which is taken along line III-III' as seen in the direction of arrows in FIG. **9**. It should be noted that elements identical to those in FIGS. **1** and **2** will be respectively denoted by the same reference numbers as those in FIGS. **1** and **2**, and their detailed explanations will be omitted.

In the fourth embodiment, a light waveguide is provided on a light-emitting portion, not below the light-emitting portion. In this regard, the fourth embodiment is different from the first embodiment. To be more specific, a Si feedback waveguide **42** is formed on an insulating film **29** for protection and a p-type contact layer **21** of a semiconductor multilayered structure **20** which forms the light-emitting portion. Also, on the p-type contact layer **21** and the insulating film **29** for protection, a Si output waveguide **43** formed of Si is provided such that the output waveguide **43** and a microring LS overlap with each other. The Si feedback waveguide **42** has the same S-shape as the Si feedback waveguide **12** of the first embodiment, and the Si output waveguide **43** has the linear shape as well as the Si output waveguide **13** of the first embodiment.

It should be noted that below the semiconductor multilayered structure **20**, either a Si substrate **10** or a GaAs substrate is provided. If the Si substrate is provided, it suffices that after the semiconductor multilayered structure **20** is formed on the GaAs substrate, it is joined to the Si substrate **10**. If the GaAs substrate is provided, it suffices that layers **21** to **25** are directly grown on the GaAs substrate without a joining method. In order to form the Si feedback waveguide **42** and the Si output waveguide **43**, it suffices that after formation of the insulating film **29**, for example, amorphous silicon or polycrystalline Si is formed, and processed to form waveguides.

Even in such a structure, because of provision of the S-shaped Si feedback waveguide **42**, the CW circulating mode can be selected, and as a result, a stable operation can be carried out. Therefore, the fourth embodiment can also obtain the same advantage as the first embodiment.

Furthermore, it may be set that as illustrated in FIG. **11**, ion implantation is carried out on inner circumferential sides of clad layers **22** and **24** which hold an active layer **23**,

thereby forming a current narrowing portion **40**. In this case, a current injection region of the microring LD can be further narrowed. Therefore, it is possible to emit light with smaller current. It should be noted that instead of ion implantation, it is possible to achieve narrowing with oxidation, and further achieve narrowing with mixing and crystallization.

Modifications

The present invention is not limited to each of the above embodiments.

The structures of the Si feedback waveguide and the Si output waveguide are not limited to the structures explained above with respect to the embodiments; i.e., it suffices that one of the CW and CCW circulating modes is set to achieve feedback. For examples, as these structures, such structures as illustrated in FIGS. **12A**, **12B** and **12C** may be applied. FIG. **12A** illustrates an example in which the distal end portion of the Si output waveguide **13** is tapered, and the Si output waveguide **13** and the semiconductor multilayered structure **20** overlap with each other at the distal end of the Si output waveguide **13**. FIG. **12B** illustrates an example in which the Si feedback waveguide **12** further comprise a Si ring resonator. FIG. **12C** illustrates an example in which the Si output waveguide **13** is connected to the C-shaped feedback waveguide **32**, whereby they are provided as a single body. In such a manner, the Si feedback waveguide and the Si output waveguide can be variously modified.

In the embodiments, the GaAs substrate is used as an element formation substrate of the light-emitting portion; however, it may be set that an InP substrate is used, and a double heterostructure in which an InAlGaAs active layer is held between InP clad layers is provided. Furthermore, the semiconductor material is not limited to the group III-V compound semiconductor, and rare-earth doped Si or GeSn can be applied as the semiconductor material.

Furthermore, with respect to the first embodiment, it is explained above that an n contact region of the light-emitting portion **20** is located outward of the ring, and with respect to the third embodiment, it is explained above that the n-type contact region of the light-emitting portion **20** is located inward of the ring; however, the n-type contact region can be located on the feedback waveguide. That is, in the first embodiment, a light-emitting portion **20** in which the contact region is located inward of the ring as in the third embodiment may be applied. Further, the structure of the light-emitting portion **20** is not necessarily limited to the double heterostructure; that is, it suffices that it has any structure as long as it emits light because of current injection.

Furthermore, it should be noted that structural features in which the distal end portion of the waveguide is tapered and the radius of curvature of the distal end is set greater than that of the ring of the light-emitting portion are advantageous in reduction of returning light and ensuring of a process margin, but they are not necessarily indispensable, and can be modified as appropriate in accordance with specifications. In addition, although with respect to the embodiments, the cross section of the waveguide is explained above by referring to a rectangular waveguide formed without leaving a Si slab, Si waveguides having other shapes, such as a rib type waveguide, may be applied.

While certain embodiments have been described, these embodiments have been presented by way of example only, and are not intended to limit the scope of the inventions. Indeed, the novel embodiments described herein may be embodied in a variety of other forms; furthermore, various

omissions, substitutions and changes in the form of the embodiments described herein may be made without departing from the spirit of the inventions. The accompanying claims and their equivalents are intended to cover such forms or modifications as would fall within the scope and spirit of the inventions.

What is claimed is:

1. A semiconductor light-emitting element comprising: a ring-shaped light-emitting portion provided on part of a substrate;
 - a mode-control light waveguide formed of Si and provided on an upper surface side or a lower surface side of the light-emitting portion, and including first and second portions located close to the light-emitting portion;
 - an output light waveguide formed of Si and provided on the upper surface side or the lower surface side of the light-emitting portion, and including a portion located close to the light-emitting portion; and
 - a nitride film or an oxide film provided between the ring-shaped light-emitting portion and the mode-control light waveguide,
- wherein the ring-shaped light-emitting portion and the mode-control light waveguide are indirectly in contact with each other through the nitride film or the oxide film, and
- wherein the mode-control light waveguide has a structure for coupling light traveling in one of a clockwise circulating mode and a counterclockwise circulating mode of the light-emitting portion, and feeding back the light in the other of the clockwise circulating mode and the counterclockwise circulating mode.
2. The element of claim 1, wherein the mode-control light waveguide is S-shaped and located inward of the light-emitting portion, and both of the first and second portions correspond to both ends of the S-shaped light waveguide.
 3. The element of claim 1, wherein the mode-control light waveguide is C-shaped and located outward of the light-emitting portion, and both of the first and second portions correspond to both ends of the C-shaped light waveguide.
 4. The element of claim 1, wherein both of the first and second portions are tapered distal end portions.
 5. The element of claim 1, wherein the mode-control light waveguide is either S-shaped or C-shaped and provided as a single body with the output light waveguide.
 6. The element of claim 1, wherein the substrate is a Si substrate, and the light-emitting portion is a group III-V compound semiconductor.
 7. The element of claim 1, wherein the light-emitting portion has a double-heterostructure in which an active layer is held between clad layers.

8. The element of claim 1, wherein the substrate is a SOI structure, and each of the light waveguides is provided by fabrication of a Si layer of the SOI substrate.
 9. The element of claim 1, wherein the light-emitting portion is joined to the substrate, in which the light waveguides are provided.
 10. The element of claim 7, wherein a current narrowing portion is provided inward of the clad layers.
 11. A semiconductor light-emitting element comprising: a ring-shaped light-emitting portion provided on part of a substrate;
 - a mode-control light waveguide formed of Si and provided on an upper surface side or a lower surface side of the light-emitting portion, and including first and second portions located close to the light-emitting portion, one or both of the first and second portions being a tapered distal end portion;
 - an output light waveguide formed of Si and provided on the upper surface side or the lower surface side of the light-emitting portion, and including a portion located close to the light-emitting portion; and
 - a nitride film or an oxide film provided between the ring-shaped light-emitting portion and the mode-control light waveguide,
- wherein the ring-shaped light-emitting portion and the mode-control light waveguide are indirectly in contact with each other through the nitride film or the oxide film, and
- wherein the mode-control light waveguide has a structure for coupling light traveling in one of a clockwise circulating mode and a counterclockwise circulating mode of the light-emitting portion, and feeding back the light in the other of the clockwise circulating mode and the counterclockwise circulating mode.
12. The element of claim 11, wherein the mode-control light waveguide is S-shaped and located inward of the light-emitting portion, and both of the first and second portions are tapered distal end portions corresponding to both ends of the S-shaped light waveguide.
 13. The element of claim 11, wherein the mode-control light waveguide is C-shaped and located outward of the light-emitting portion, and both of the first and second portions are tapered distal end portions corresponding to both ends of the C-shaped light waveguide.
 14. The element of claim 11, wherein the mode-control light waveguide is either S-shaped or C-shaped and provided as a single body with the output light waveguide.
 15. The element of claim 11, wherein the light-emitting portion has a double-heterostructure in which an active layer is held by clad layers, and a current narrowing portion is provided inward of the clad layers.

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